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捷多邦,专业PCB打样工厂,24少时加急

2SA2021

Silicon PNP epitaxial planer type

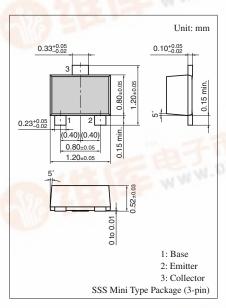
For general amplification Complementary to 2SC5609

Features

- High foward current transfer ratio h_{FE}
- SSS-mini type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

ParameterSymbolRatingUnitCollector to base voltage V_{CBO} -60VCollector to emitter voltage V_{CEO} -50VEmitter to base voltage V_{EPO} -7V	~ ~ ~					
$\frac{1}{\text{Collector to emitter voltage}} \frac{1}{\text{V}_{\text{CEO}}} \frac{1}{-50} \text{V}$	Parameter	Symbol	Rating	Unit		
	Collector to base voltage	V _{CBO}	-60	v		
Emitter to base voltage $V_{\rm EPO}$ -7 V	Collector to emitter voltage	V _{CEO}	-50	V		
EBO EBO	Emitter to base voltage	V _{EBO}	-7	V		
Peak collector current I _{CP} -200 mA	Peak collector current	I _{CP}	-200	mA		
Collector current I _C -100 mA	Collector current	I _C	-100	mA		
Collector power dissipation P _C 100 mW	Collector power dissipation	P _C	100	mW		
Junction temperature T _j 125 °C	Junction temperature	Tj	125	°C		
Storage temperature T_{stg} -55 to +125 °C	Storage temperature	T _{stg}	-55 to +125	°C		

Absolute Maximum Ratings $T_a = 25^{\circ}C$



Marking Symbol: 3E

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff current	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μA
	I _{CEO}	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	μΑ
Collector to base voltage	V _{CBO}	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$	-60			V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = -100 \ \mu A, \ I_{\rm B} = 0$	-50		10 11	V
Emitter to base voltage	V _{EBO}	$I_{\rm E} = -10 \mu {\rm A}, I_{\rm C} = 0$	-7			V
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, \text{ I}_{C} = -2 \text{ mA}$	180		390	
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$		- 0.3	- 0.5	V
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2.7		pF
Transition frequency	f_{T}	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz



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